

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = 25^\circ C$
-20V	54m $\Omega$ @ $V_{GS} = -4.5V$	-2.5A
	90m $\Omega$ @ $V_{GS} = -1.8V$	-1.8A

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

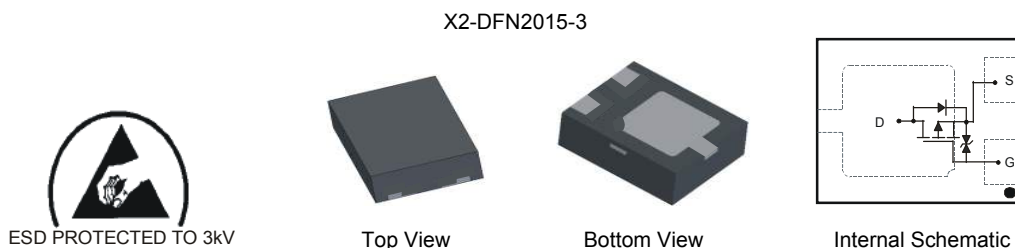
- Backlighting
- Power Management Functions
- DC-DC Converters
- 

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device, Halogen and Antimony Free (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

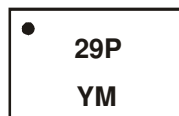


## Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2069UFY4-7	X2-DFN2015-3	3000/Tape & Reel

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



29P = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 4)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	-2.5	A
		T <sub>A</sub> = 70°C		-2.2	
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-12	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P <sub>D</sub>	0.53	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C	R <sub>θJA</sub>	231	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	μA	T <sub>J</sub> = 25°C, V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.3	-0.55	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	36	54	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.5A
			46	69		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.2A
			60	90		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	8	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.5A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	214	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	104	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	25	—	pF	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Gate Resonance	R <sub>g</sub>	—	250	—	Ω	
<b>SWITCHING CHARACTERISTICS (Note 7)</b>						
Total Gate Charge	Q <sub>g</sub>	—	9.1	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -4A
Gate-Source Charge	Q <sub>gs</sub>	—	1.5	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.7	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	80.4	160	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>D</sub> = 2.5Ω, R <sub>G</sub> = 3.0Ω
Turn-On Rise Time	t <sub>r</sub>	—	155.1	210	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	688.1	1376	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	423.8	848	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

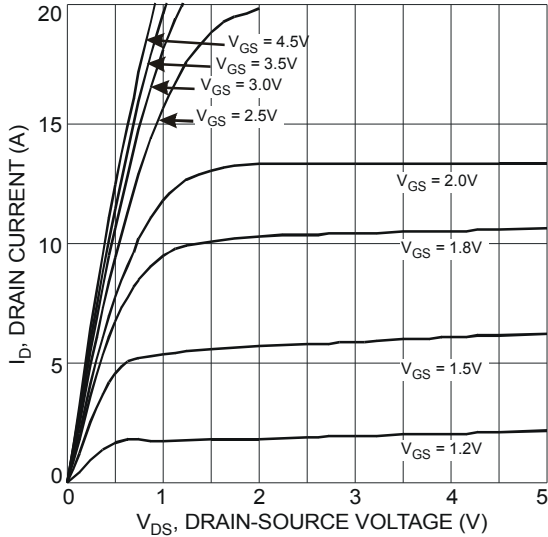


Fig. 1 Typical Output Characteristic

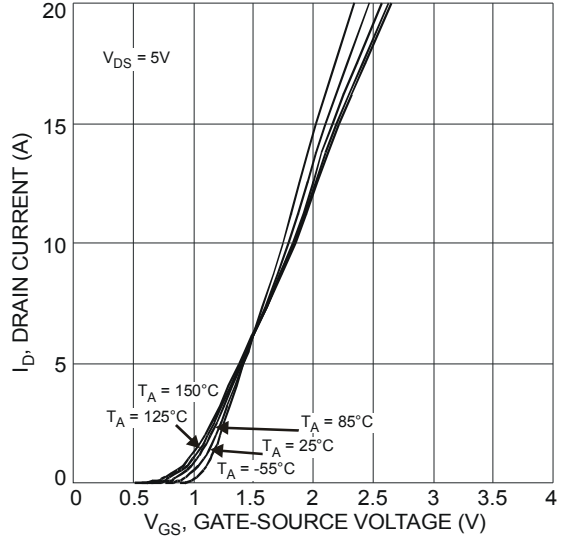


Fig. 2 Typical Transfer Characteristic

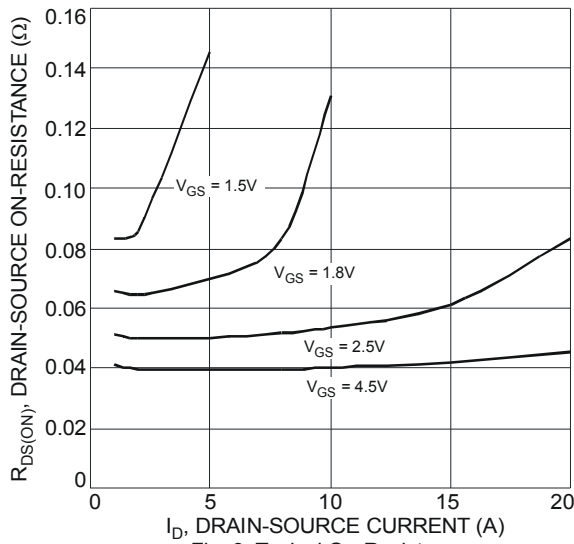


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

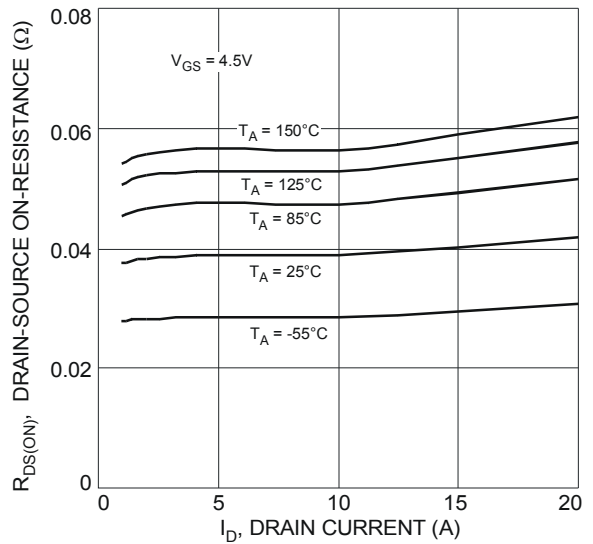


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

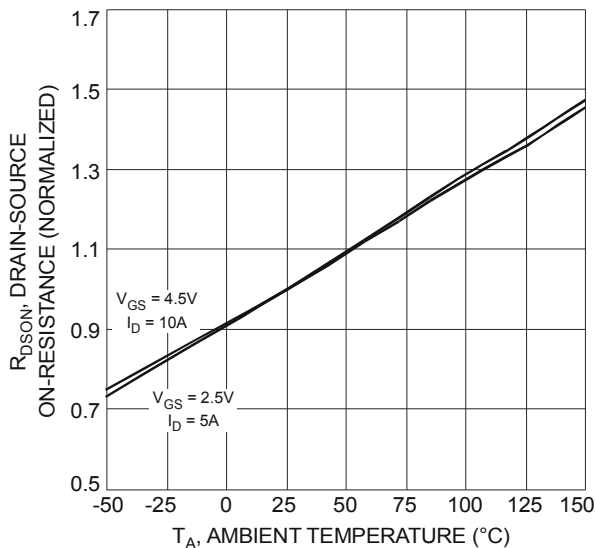


Fig. 5 On-Resistance Variation with Temperature

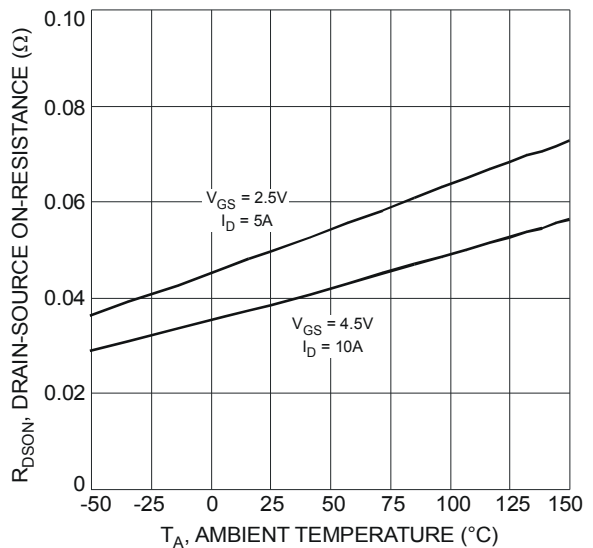


Fig. 6 On-Resistance Variation with Temperature

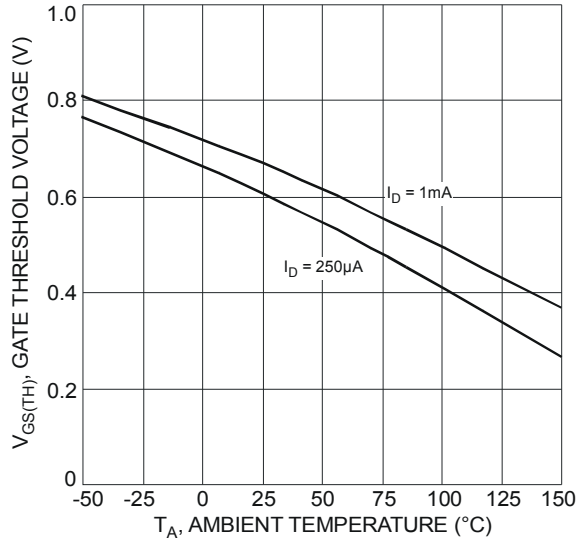


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

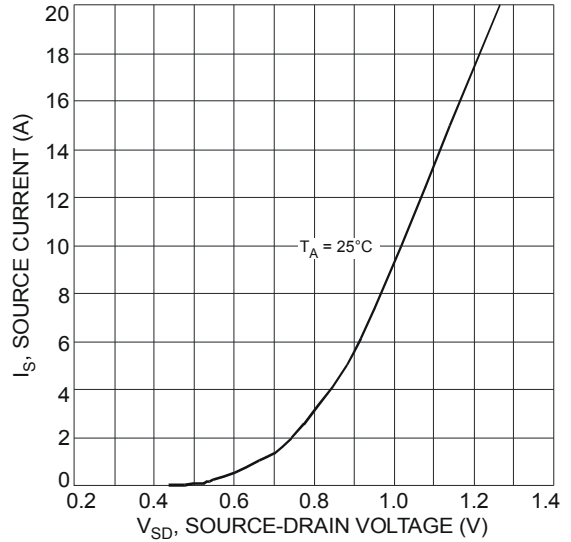


Fig. 8 Diode Forward Voltage vs. Current

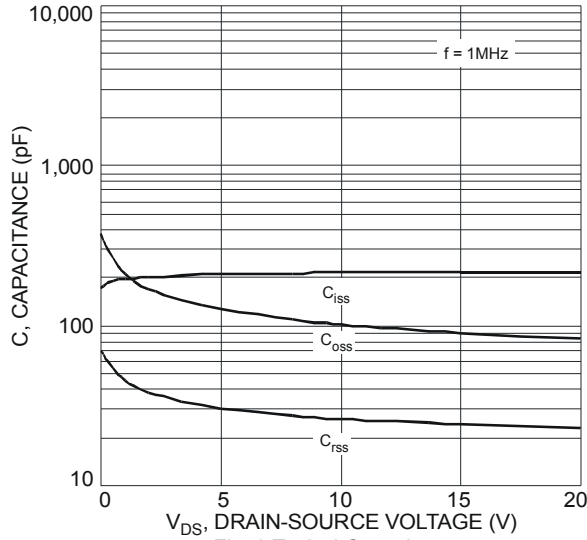


Fig. 9 Typical Capacitance

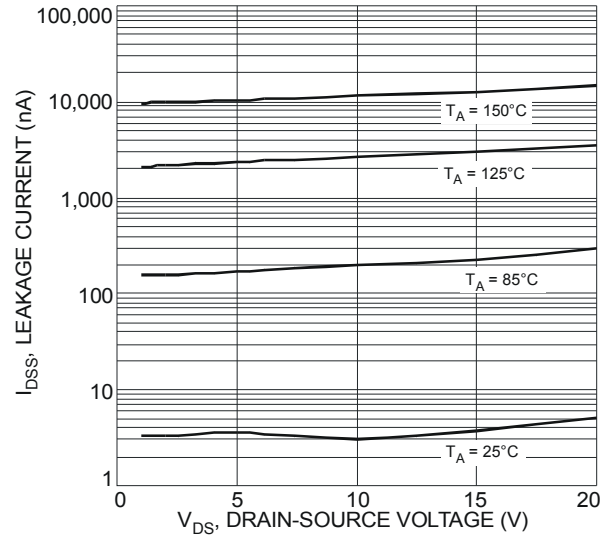


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

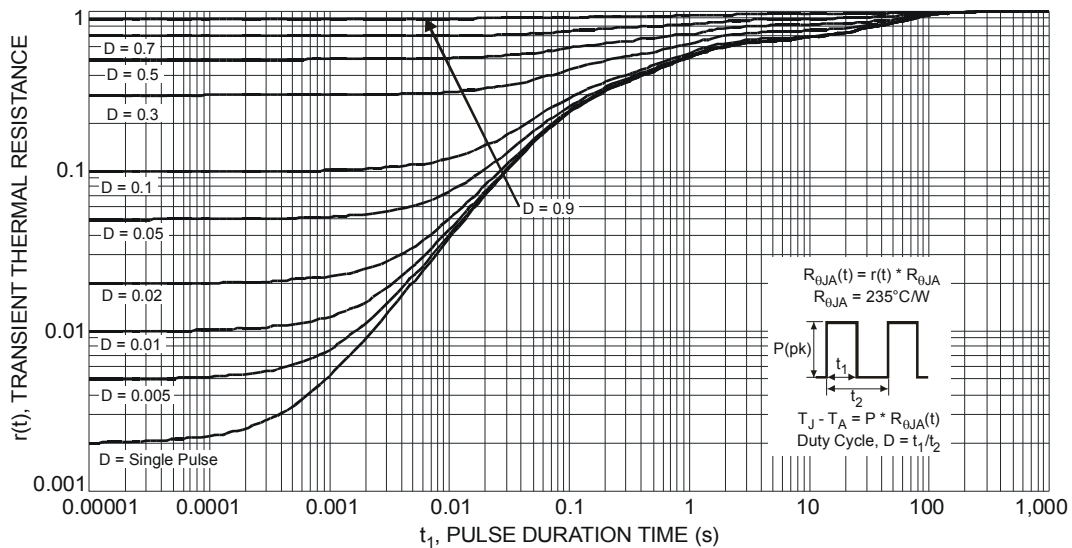
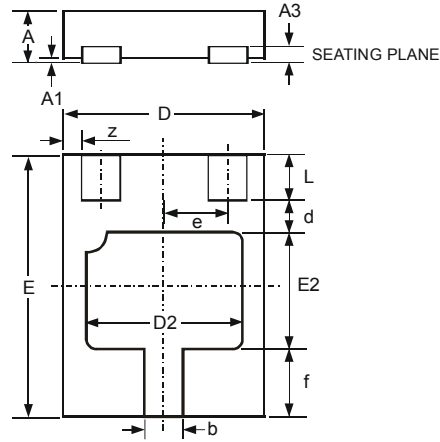


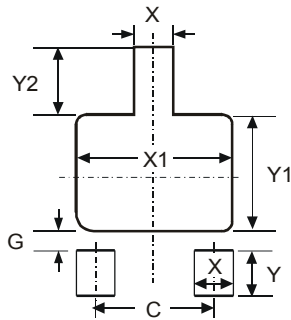
Fig. 11 Transient Thermal Response

**Package Outline Dimensions**



X2-DFN2015-3			
Dim	Min	Max	Typ
A	-	0.40	-
A1	0	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
d	-	-	0.30
D	1.45	1.575	1.50
D2	1.00	1.20	1.10
e	-	-	0.50
E	1.95	2.075	2.00
E2	0.70	0.90	0.80
f	-	-	0.60
L	0.25	0.35	0.30
z	-	-	0.125
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
C	1.00
G	0.15
X	0.31
X1	1.30
Y	0.50
Y1	1.00
Y2	0.65

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